

Dual N-channel TrenchMOS logic level FET

Rev. 04 — 27 April 2010

Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

Low conduction losses due to low on-state resistance

1.3 Applications

- Battery chargers
- DC-to-DC convertors

1.4 Quick reference data

- Suitable for logic level gate drive sources
- Notebook computers
- Portable equipment

| Table 1. | Quick reference data | | | | | |
|-------------------|----------------------------------|--|-----|-----|------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 150 °C | - | - | 20 | V |
| I _D | drain current | $T_{sp} = 25 \text{ °C}$; Single device conducting; see <u>Figure 1</u> ; see <u>Figure 3</u> | - | - | 10.9 | A |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; see <u>Figure 2</u> | - | - | 4.17 | W |
| Static cha | aracteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V_{GS} = 2.5 V; I_D = 3 A; T_j = 25 °C | - | 25 | 35 | mΩ |
| Dynamic | characteristics | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 5 \text{ V}; I_D = 6 \text{ A}; V_{DS} = 16 \text{ V};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 11}{1}$ | - | 6 | - | nC |



Dual N-channel TrenchMOS logic level FET

2. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|--------------------|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | S1 | source1 | | |
| 2 | G1 | gate1 | | |
| 3 | S2 | source2 | | |
| 4 | G2 | gate2 | | |
| 5 | D2 | drain2 | | |
| 6 | D2 | drain2 | SOT96-1 (SO8) | S1 G1 S2 G2 |
| 7 | D1 | drain1 | | mbk725 |
| 8 | D1 | drain1 | | |

3. Ordering information

| Table 3. Ordering information | | | | |
|-------------------------------|---------|---|---------|--|
| Type number | Package | | | |
| | Name | Description | Version | |
| PHKD6N02LT | SO8 | plastic small outline package; 8 leads; body width 3.9 mm | SOT96-1 | |

4. Limiting values

Table 4. Limiting values

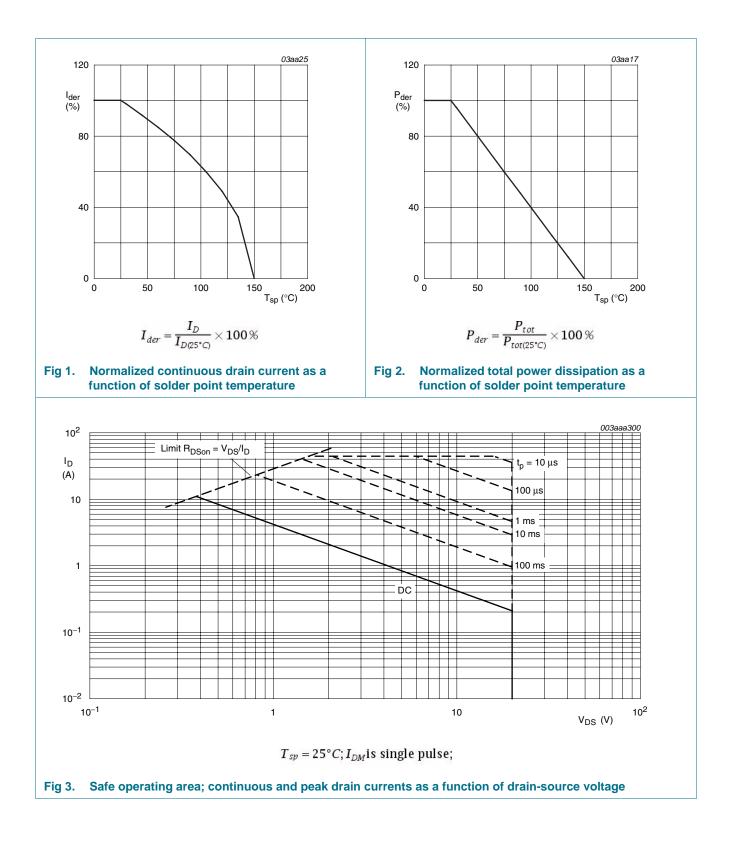
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 150 °C | - | - | 20 | V |
| V _{DGR} | drain-gate voltage | $T_j \le 150 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | - | 20 | V |
| V _{GS} | gate-source voltage | | -12 | - | 12 | V |
| I _D | drain current | T _{sp} = 100 °C; Single device conducting; see <u>Figure 1</u> | - | - | 6.8 | A |
| | | $T_{sp} = 25 \text{ °C}$; Single device conducting; see <u>Figure 1</u> ; see <u>Figure 3</u> | - | - | 10.9 | А |
| I _{DM} | peak drain current | $T_{sp} = 25 \text{ °C}; t_p \le 100 \mu\text{s}; \text{ pulsed}; \text{ Single}$ device conducting; see <u>Figure 3</u> | - | - | 44 | А |
| P _{tot} | total power dissipation | T _{sp} = 25 °C; see <u>Figure 2</u> | - | - | 4.17 | W |
| T _{stg} | storage temperature | | -55 | - | 150 | °C |
| Tj | junction temperature | | -55 | - | 150 | °C |
| Source-drain | diode | | | | | |
| ls | source current | T _{sp} = 25 °C | - | - | 3.5 | А |
| I _{SM} | peak source current | $T_{sp} = 25 \text{ °C}; t_p \le 10 \mu\text{s}; \text{ pulsed}$ | - | - | 44 | А |

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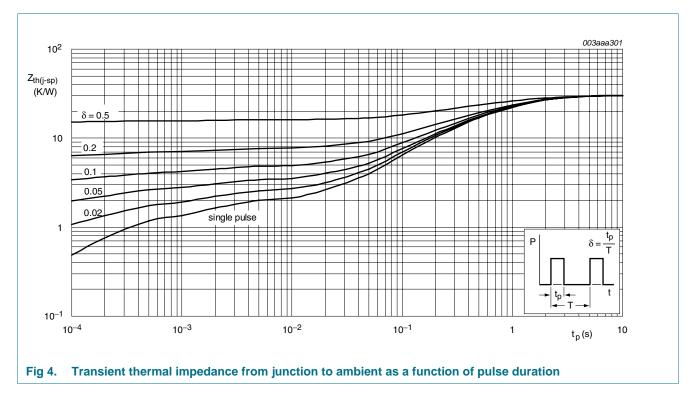
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5. Thermal characteristics

| Table 5. | Thermal characteristics | | | | | |
|-----------------------|--|--|-----|-----|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| R _{th(j-sp)} | thermal resistance from junction to solder point | see Figure 4 | - | - | 30 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | minimum footprint; mounted on printed-circuit board | - | 70 | - | K/W |



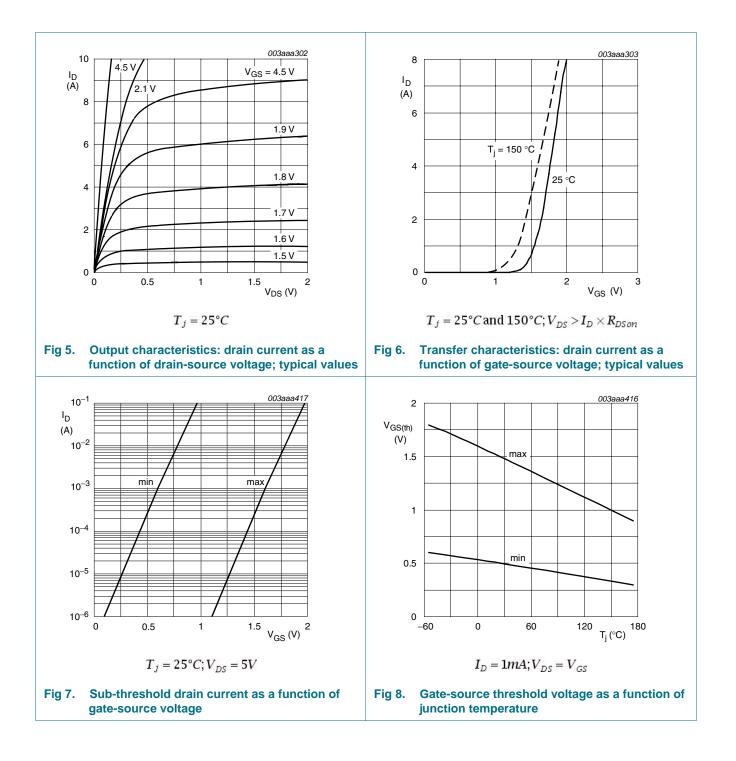
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6. Characteristics

| Table 6. | Characteristics | | | | | |
|--|-----------------------------------|--|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| Static cha | aracteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$ | 20 | - | - | V |
| V _{GS(th)} | gate-source threshold voltage | I _D = 250 μA; V _{DS} = 10 V; T _j = 25 °C; see <u>Figure 8</u> | 0.5 | - | 1.5 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | 0.05 | 10 | μΑ |
| | | $V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$ | - | - | 500 | μΑ |
| I _{GSS} | gate leakage current | V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| | | V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 °C | - | - | 100 | nA |
| R _{DSon} drain-source resistance | drain-source on-state | V_{GS} = 2.5 V; I_D = 3 A; T_j = 25 °C | - | 25 | 35 | mΩ |
| | resistance | V _{GS} = 5 V; I _D = 3 A; T _j = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u> | - | - | 35 | mΩ |
| | | V _{GS} = 5 V; I _D = 3 A; T _j = 25 °C; see <u>Figure 9;</u> see <u>Figure 10</u> | - | 16 | 20 | mΩ |
| Dynamic | characteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 6 \text{ A}; V_{DS} = 16 \text{ V}; V_{GS} = 5 \text{ V}; T_j = 25 \text{ °C};$ | - | 15.3 | - | nC |
| Q _{GS} | gate-source charge | see <u>Figure 11</u> | - | 2.2 | - | nC |
| Q_{GD} | gate-drain charge | | - | 6 | - | nC |
| C _{iss} | input capacitance | $V_{DS} = 10 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$ | - | 950 | - | pF |
| C _{oss} | output capacitance | see <u>Figure 12</u> | - | 355 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 256 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = 10 V; R_{L} = 3.3 Ω; V_{GS} = 5 V; | - | 15 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \ \Omega; \ T_j = 25 \ ^{\circ}C$ | - | 49 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 50 | - | ns |
| t _f | fall time | | - | 23 | - | ns |
| Source-d | rain diode | | | | | |
| V _{SD} | source-drain voltage | $I_S = 6 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$ | - | - | 1.2 | V |
| t _{rr} | reverse recovery time | $I_{S} = 6 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ | - | 40 | - | ns |
| Q _r | recovered charge | V _{DS} = 20 V; T _j = 25 °C | - | 7 | - | nC |

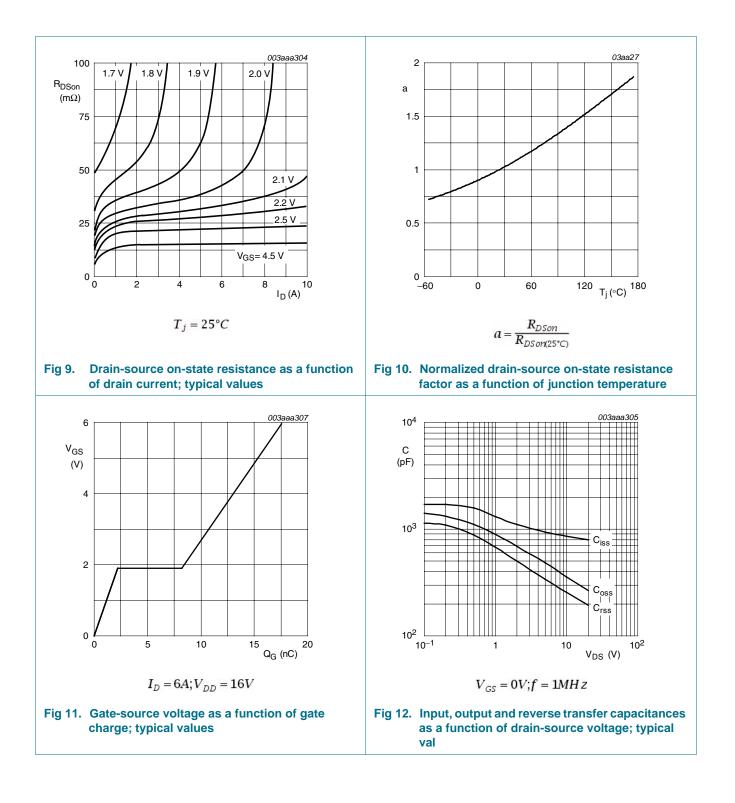
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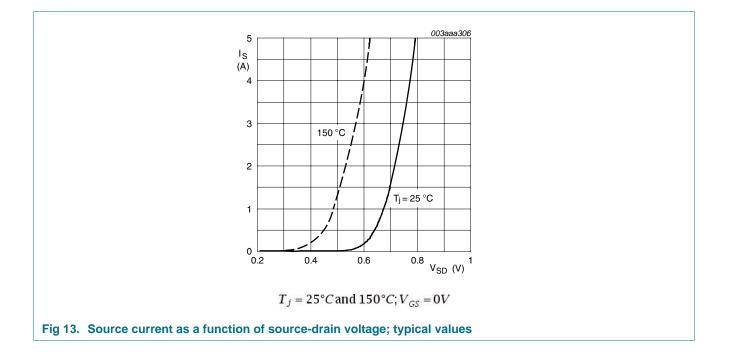


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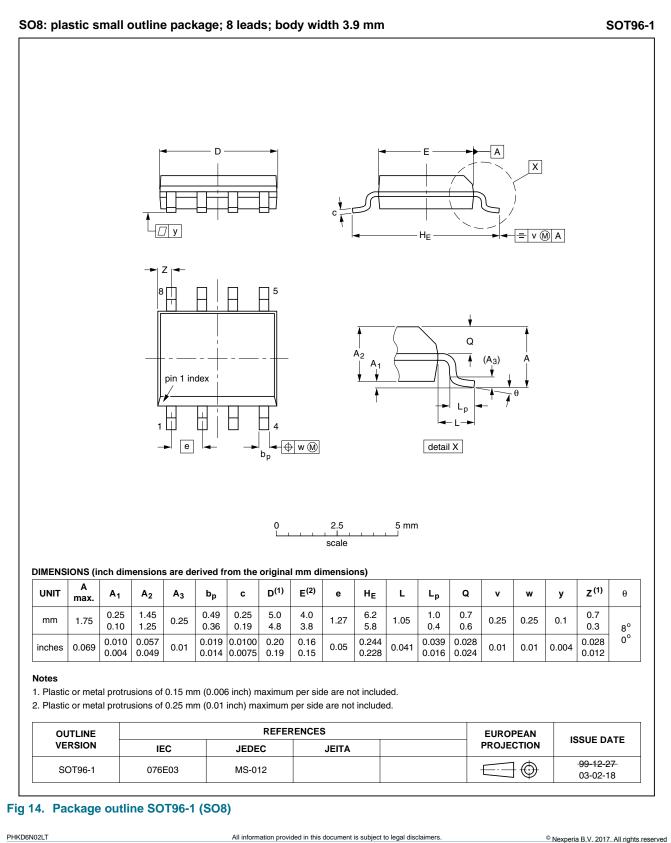
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Dual N-channel TrenchMOS logic level FET



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7. Package outline



PHKD6N02LT Product data sheet

Dual N-channel TrenchMOS logic level FET

8. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|---------------------------------|--------------------|---------------|---------------|
| PHKD6N02LT_4 | 20100427 | Product data sheet | - | PHKD6N02LT_3 |
| Modifications: | Various cha | anges to content. | | |
| PHKD6N02LT_3 | 20091119 | Product data sheet | - | PHKD6N02LT-02 |
| PHKD6N02LT-02 | 20030812 | Product data | - | PHKD6N02LT-01 |
| PHKD6N02LT-01 | 20010907 | Product data | - | - |

PHKD6N02LT

Dual N-channel TrenchMOS logic level FET

9. Legal information

9.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Dual N-channel TrenchMOS logic level FET

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Dual N-channel TrenchMOS logic level FET

11. Contents

| 1 | Product profile1 |
|-----|--------------------------|
| 1.1 | General description1 |
| 1.2 | Features and benefits1 |
| 1.3 | Applications1 |
| 1.4 | Quick reference data1 |
| 2 | Pinning information2 |
| 3 | Ordering information2 |
| 4 | Limiting values2 |
| 5 | Thermal characteristics4 |
| 6 | Characteristics5 |
| 7 | Package outline9 |
| 8 | Revision history10 |
| 9 | Legal information11 |
| 9.1 | Data sheet status11 |
| 9.2 | Definitions11 |
| 9.3 | Disclaimers |
| 9.4 | Trademarks12 |
| 10 | Contact information12 |

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